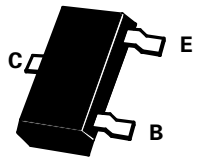
SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

FMMTA92

ISSUE 4 - MARCH 2001 ✪

PARTMARKING DETAILS: – FMMTA92 - 4E
– FMMTA92R - 8E

COMPLEMENTARY TYPES: – FMMTA92 - FMMTA42



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMTA92	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-200	mA
Power Dissipation at T_{amb}= 25°C	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

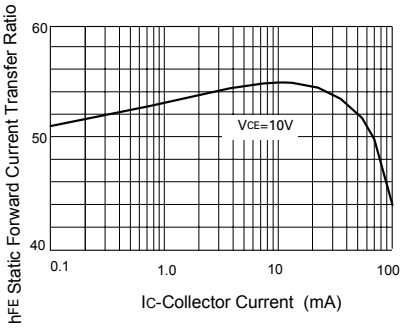
PARAMETER	SYMBOL	FMMTA92 MIN.	FMMTA92 MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300		V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300		V	I_C=-1mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	I_E=-100μA, I_C=0
Collector Cut-Off Current	I_{CBO}		-0.25 μA	μA μA	V_{CB}=-200V, I_E=0 V_{CB}=-160V, I_E=0-
Emitter Cut-Off Current	I_{EBO}		-0.1	μA	V_{EB}=-3V, I_E=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.5	V	I_C=-20mA, I_B=-2mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	V	I_C=-20mA, I_B=-2mA*
Static Forward Current Transfer Ratio	h_{FE}	25 40 25			I_C=-1mA, V_{CE}=10V* I_C=-10mA, V_{CE}=10V* I_C=-30mA,V_{CE}=-10V*
Transition Frequency	f_T	50		MHz	I_C=-10mA, V_{CE}=-20V f=20MHz
Output Capacitance	C_{obo}		6	pF	V_{CB}=-20V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

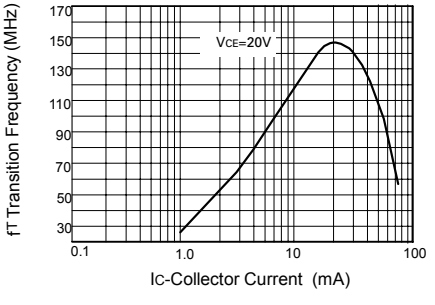
ZETEX

FMMTA92

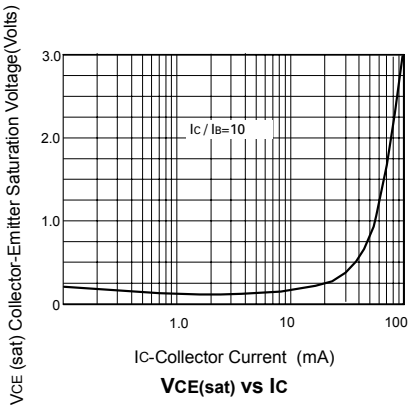
TYPICAL CHARACTERISTICS



hFE v IC



fT vs IC



VCE(sat) vs IC